

## Silicon Standard Recovery Diode

$V_{RRM} = 400\text{ V} - 1600\text{ V}$   
 $I_F = 25\text{ A}$

### Features

- High Surge Capability
- Types up to 1600 V  $V_{RRM}$
- Equivalent to SKN26 Series
- Not ESD Sensitive

DO-4 Package



### Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified (GKR has leads reversed)

Parameter	Symbol	Conditions	GKN26/04	GKN26/08	GKN26/12	GKN26/14	GKN26/16	Unit
Repetitive peak reverse voltage	$V_{RRM}$		400	800	1200	1400	1600	V
DC blocking voltage	$V_{DC}$		400	800	1200	1400	1600	V
Continuous forward current	$I_F$	$T_C \leq 100\text{ }^\circ\text{C}$	25	25	25	25	25	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$	375	375	375	375	375	A
Operating temperature	$T_j$		-55 to 150	-55 to 150	-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-55 to 150	-55 to 150	-55 to 150	-55 to 150	-55 to 150	$^\circ\text{C}$

### Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	GKN26/04	GKN26/08	GKN26/12	GKN26/14	GKN26/16	Unit
Diode forward voltage	$V_F$	$I_F = 60\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	1.55	1.55	1.55	1.55	1.55	V
Reverse current	$I_R$	$V_R = V_{RRM}$ , $T_j = 180\text{ }^\circ\text{C}$	4	4	4	4	4	mA

### Thermal characteristics

Parameter	Symbol	Conditions	GKN26/04	GKN26/08	GKN26/12	GKN26/14	GKN26/16	Unit
Thermal resistance, junction - case	$R_{thJC}$		2.00	2.00	2.00	2.00	2.00	K/W

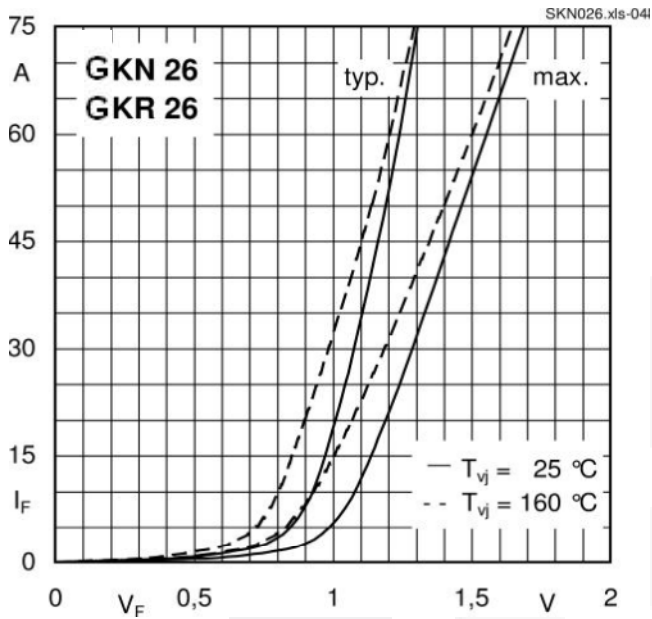


Fig 1: Forward Characteristics

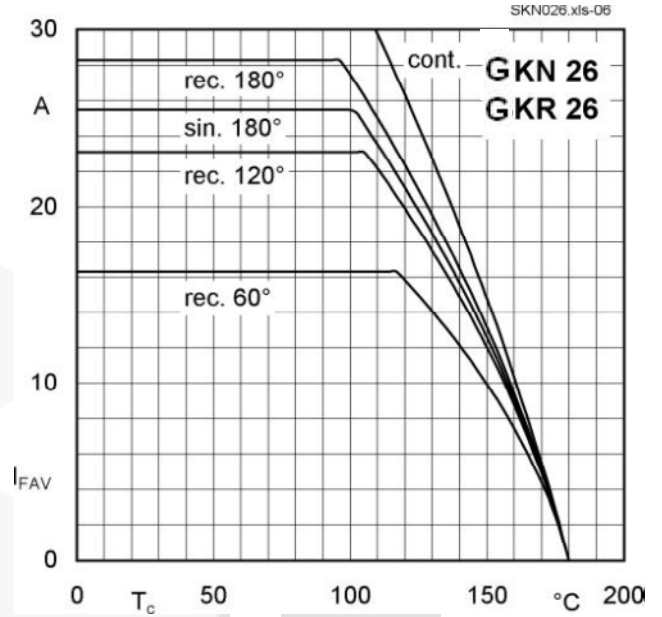


Fig 2: Forward Current vs Case Temp

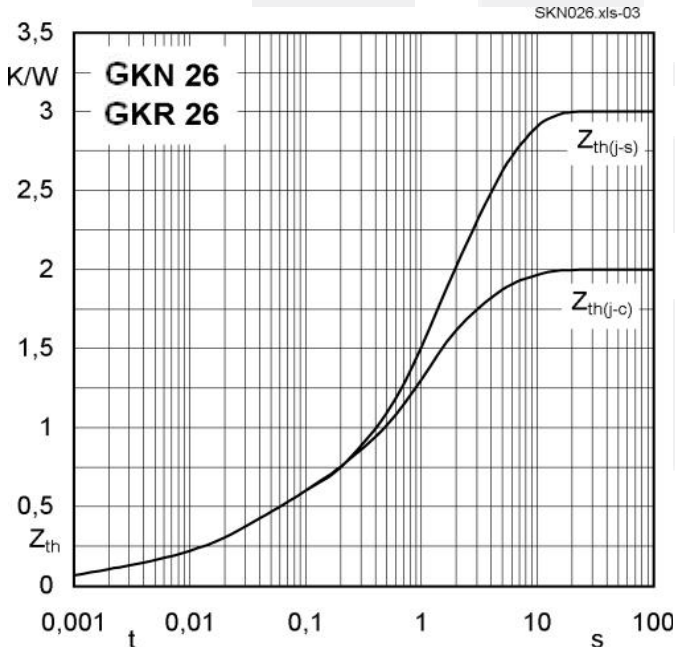


Fig 3: Transient Thermal Impedance vs Time

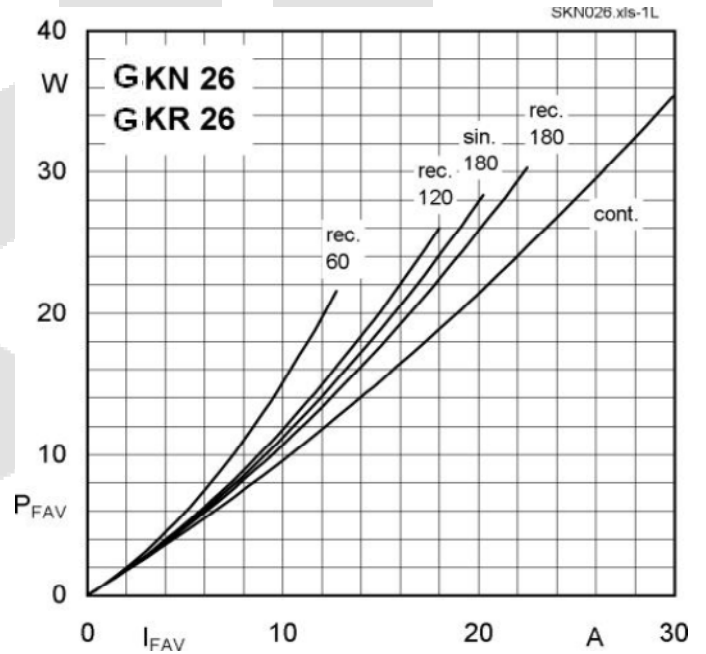
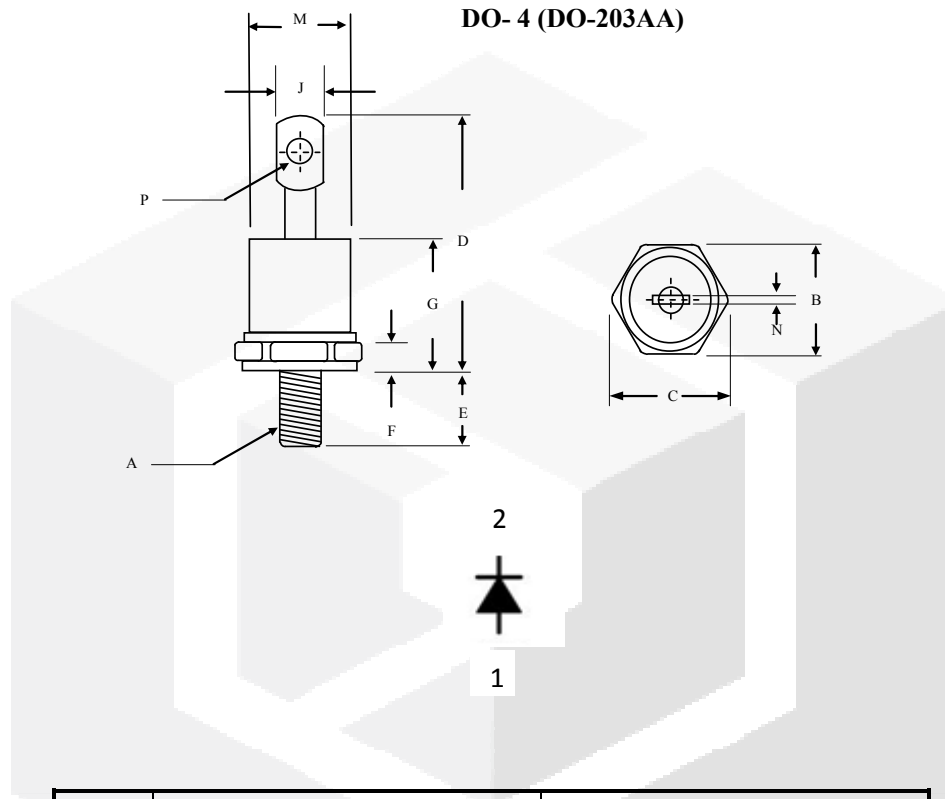


Fig 4: Power Dissipation vs Forward Current

**Package dimensions and terminal configuration**

Product is marked with part number and terminal configuration.



	Inches		Millimeters	
	Min	Max	Min	Max
A	10-32 UNF			
B	0.424	0.437	10.77	11.10
C	----	0.505	----	12.82
D	----	0.800	----	20.30
E	0.453	0.492	11.50	12.50
F	0.114	0.140	2.90	3.50
G	----	0.405	----	10.29
J	----	0.216	----	5.50
M	----	φ0.302	----	φ7.68
N	0.031	0.045	0.80	1.15
P	0.070	0.79	1.80	2.00

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